TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPC8061-H**

High Efficiency DC-DC Converter Applications
Notebook PC Applications
Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 3.5 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS}(ON) = 21 \text{ m}\Omega \text{ (typ.) } (V_{GS} = 4.5 \text{ V})$ 

- Low leakage current:  $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.1 mA)

## **Absolute Maximum Ratings (Ta = 25°C)**

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	30	V	
Drain-gate voltage (R	$k_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	30	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub>	8	Α	
Drain current	Pulsed (Note 1)	I <sub>DP</sub>	32		
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	$P_{D}$	1.9	W	
Drain power dissipation $(t = 10 s)$ (Note 2b)		$P_{D}$	1.0	W	
Single pulse avalanch	ne energy (Note 3)	E <sub>AS</sub>	42	mJ	
Avalanche current		I <sub>AR</sub>	8	Α	
Repetitive avalanche	energy Note 2a) (Note 4)	E <sub>AR</sub>	0.21	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

Unit: mm

4.9±0.2

4.9±0.2

4.9±0.2

4.9±0.2

1,2,3:SOURCE 4:GATE 5,6,7,8:DRAIN

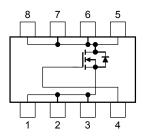
JEDEC —

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TOSHIBA 2-5R1A

Weight: 0.085 g (typ.)

#### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

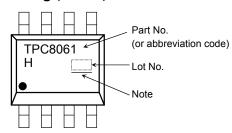
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

### Marking (Note 5)

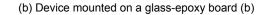


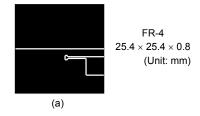
Note: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

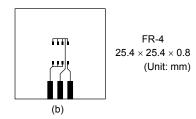
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)



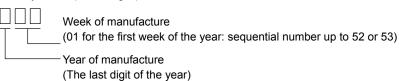




Note 3:  $V_{DD} = 24~V,~T_{ch} = 25^{\circ}C$  (initial),  $L = 500~\mu H,~R_G = 25~\Omega,~I_{AR} = 8~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



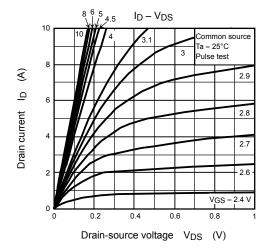


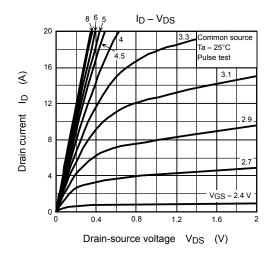
## **Electrical Characteristics (Ta = 25°C)**

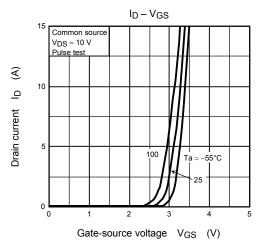
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_		±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	10	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
Diain-source bre	akdown voltage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_	v
Gate threshold ve	oltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 0.1 \text{ mA}$	1.3	_	2.3	V
Drain sauras ON	resistance.	D	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 4 A	_	21	29	0
Drain-source ON	-resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A	_	—     18     26       —     630     —       —     46     —		mΩ
Input capacitance	e	C <sub>iss</sub>		_	630	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	46	_	pF
Output capacitan	ce	Coss		_	150	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	_	1.4	_	Ω
Switching time	Rise time	t <sub>r</sub>	VGS 10 V	_	2.6	_	- ns
	Turn-on time	t <sub>on</sub>		_	7.6	_	
	Fall time	t <sub>f</sub>		_	2.9	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx 15 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \mu\text{s}$	_	18	_	
Total gate charge	Fotal gate charge		$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$	_	11	_	
(gate-source plus	s gate-drain)	$Q_g$ $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 0$		_	6.2	_	nC
Gate-source charge 1		Q <sub>gs1</sub>	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$	_	2.3	_	
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	2.5	_	
Gate switch charge		Q <sub>SW</sub>		_	3.5	_	

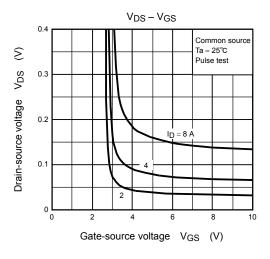
# Source-Drain Ratings and Characteristics (Ta = 25°C)

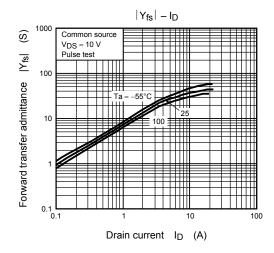
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	32	Α
Forward voltage (diode)			V <sub>DSF</sub>	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

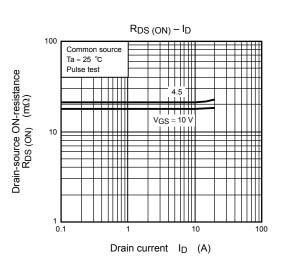




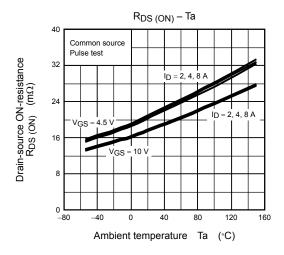


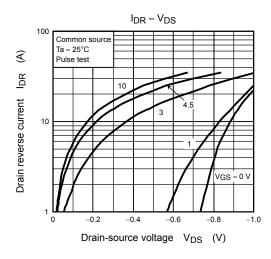


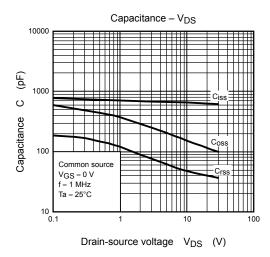


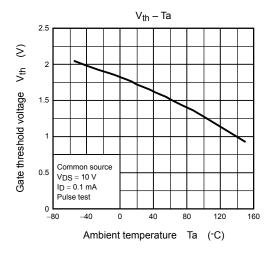


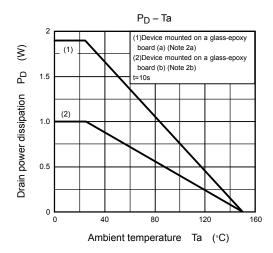
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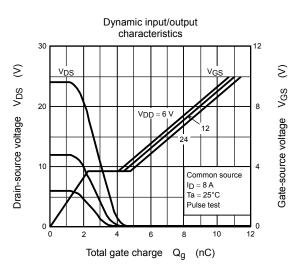




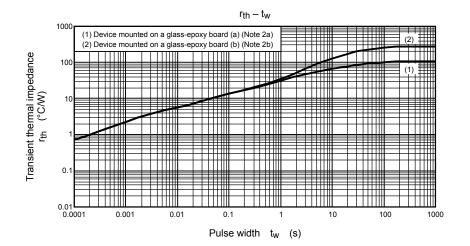


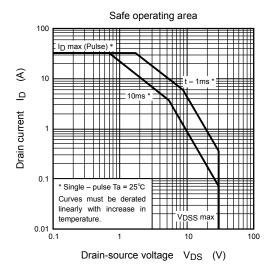






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